

AMENDMENTS TO THE CLAIMS:

Please amend the claims as indicated in listing of claims provided below. This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously presented) A method for producing a semiconductor device comprising:
forming wiring using a first solution ejector for ejecting a conductive material,
forming a resist mask on the wiring using a second solution ejector, and
etching the wiring using an atmospheric-pressure plasma device having a linear plasma generator using the resist mask as a mask.

2. (Canceled)

3. (Previously presented) A method for producing a semiconductor device comprising:
forming wiring,
forming a resist mask at least on the wiring using a solution ejector, and
etching the wiring using an atmospheric-pressure plasma device having a linear plasma generator using the resist mask as a mask.

4. (Currently Amended) The method for producing the semiconductor device in any one of claim 1 [[to]] and claim 3, wherein the solution ejector has one or more of solution ejection ports.

5. (Currently Amended) The method for producing the semiconductor device in any one of claim 1 [[to]] and claim 3, wherein when a wiring material, or a resist, or the like is ejected using the solution ejector, a substrate is heated.

6. (Currently Amended) The method for producing the semiconductor device in any one of claim 1 [[to]] and claim 3, wherein the etching and/or ashing are/is processed at the atmospheric pressure or near-atmospheric pressure.

7. (Withdrawn) A method for producing a display device using a semiconductor device comprising:

forming wiring using a first solution ejector for ejecting a conductive material,
forming a resist mask on the wiring using a second solution ejector, and
etching the wiring using an atmospheric-pressure plasma device having a linear plasma generator using the resist mask as a mask.

8. (Withdrawn) A method for producing a display device using a semiconductor device comprising:

forming wiring using a solution ejector for ejecting a conductive material,
forming a resist mask at least on the wiring, and
etching the wiring using an atmospheric-pressure plasma device having a linear plasma generator using the resist mask as a mask.

9. (Withdrawn) A method for producing a display device using a semiconductor device comprising:

forming wiring,
forming a resist mask at least on the wiring using a solution ejector, and
etching the wiring using an atmospheric-pressure plasma device having a linear plasma generator using the resist mask as a mask.

10. (Withdrawn) The method for producing the display device using the semiconductor device in any one of claim 7 to claim 9, wherein the solution ejector has one or more of solution ejection ports.

11. (Withdrawn) The method for producing the display device using the semiconductor device in any one of claim 7 to claim 9, wherein when a solution is ejected using the solution ejector, a substrate is heated.

12. (Withdrawn) The method for producing the display device using the

semiconductor device in any one of claim 7 to claim 8, wherein the etching and/or the ashing are/is processed at the atmospheric pressure or near-atmospheric pressure.

13. (Previously presented) A method for producing a semiconductor device comprising:
forming wiring using a first solution ejector for ejecting a conductive material,
forming a resist mask on the wiring using a second solution ejector, and
etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask.

14. (Previously presented) A method for producing a semiconductor device comprising:
forming wiring using a solution ejector for ejecting a conductive material,
forming a resist mask at least on the wiring, and
etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask.

15. (Previously presented) A method for producing a semiconductor device comprising:
forming wiring,
forming a resist mask at least on the wiring using a solution ejector, and
etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask.

16. (Previously presented) The method for producing the semiconductor device in any one of claim 13 to claim 15, wherein the solution ejector has one or more of solution ejection ports.

17. (Previously presented) The method for producing the semiconductor device in any one of claim 13 to claim 15, wherein when a wiring material, or a resist, or the like is ejected using the solution ejector, a substrate is heated.

18. (Previously presented) The method for producing the semiconductor device in any one of claim 13 to claim 15, wherein the etching is processed at the atmospheric pressure or near-atmospheric pressure.

19. (Withdrawn) A method for producing a display device using a semiconductor device comprising:
forming wiring using a first solution ejector for ejecting a conductive material,
forming a resist mask on the wiring using a second solution ejector, and
etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask.

20. (Withdrawn) A method for producing a display device using a semiconductor device comprising:
forming wiring using a solution ejector for ejecting a conductive material,
forming a resist mask at least on the wiring, and
etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask.

21. (Withdrawn) A method for producing a display device using a semiconductor device comprising:
forming wiring,
forming a resist mask at least on the wiring using a solution ejector, and
etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask.

22. (Withdrawn) A method for producing the display device using the semiconductor device in any one of claim 19 to claim 21, wherein the solution ejector has one or more of solution ejection ports.

23. (Withdrawn) A method for producing the display device using the semiconductor

device in any one of claim 19 to claim 21, wherein when a solution is ejected using the solution ejector, a substrate is heated.

24. (Withdrawn) A method for producing the display device using the semiconductor device in any one of claim 19 to claim 21, wherein the etching is processed at the atmospheric pressure or near-atmospheric pressure.